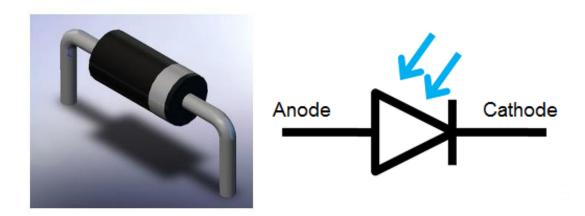


#### **Lecture 16: Introduction to Diodes**

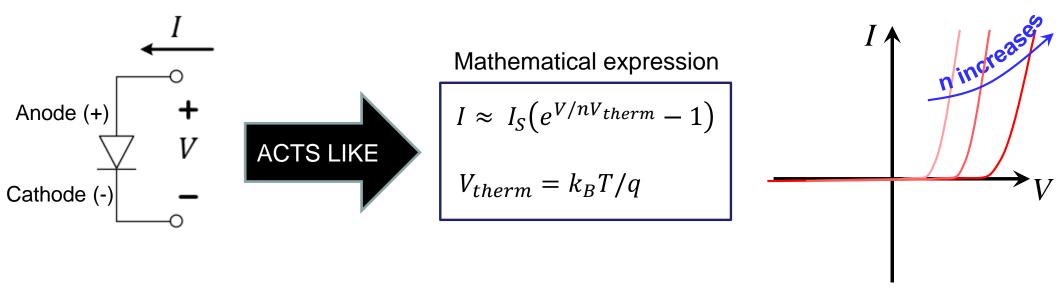
- Diode IV characteristics
- Connecting diode to a linear circuit
- Piecewise linear models of diodes



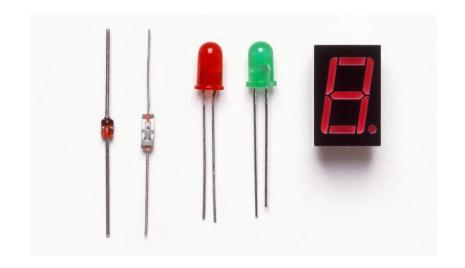
Recommended: https://learn.sparkfun.com/tutorials/diodes



#### **■ IV** characteristics



#### ■ Major applications: lighting, electronics



Made of *semiconductor* materials like Si, Ge, GaN with some additives called *dopants*.



#### ■ Date sheet

$$I \approx I_S(e^{V/nV_{therm}}-1)$$

$$V_{therm} = \frac{k_B T}{q}$$
 (thermal voltage)

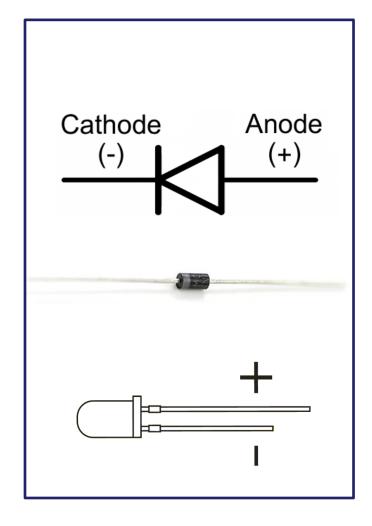
$$\frac{k_B}{q} = 8.617 \times 10^{-5} eV \cdot K^{-1}$$
 (Boltzmann's constant)

T = temperature (Kelvin)

$$\frac{k_B T}{q} = 25.85 mV$$
 at 300K

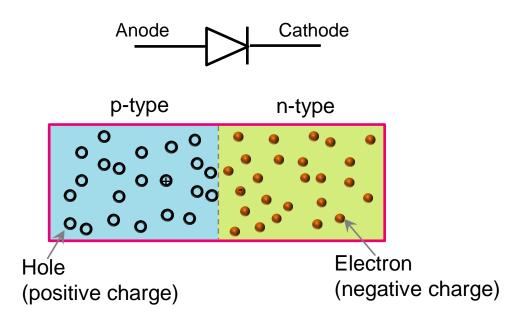
n = ideal factor (depends on device fabrication parameters)

#### Circuit model





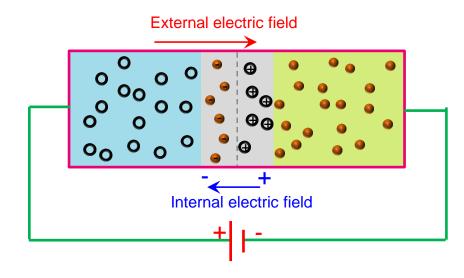
#### **Working principle – Supplementary Note**



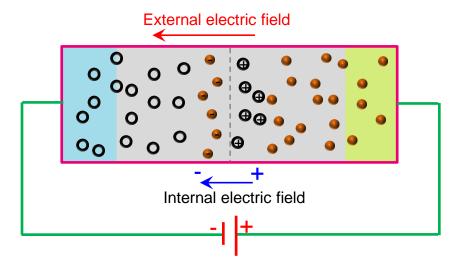
depletion layer
PN junction

Internal electric field

Case 1: forward bias (conductive)

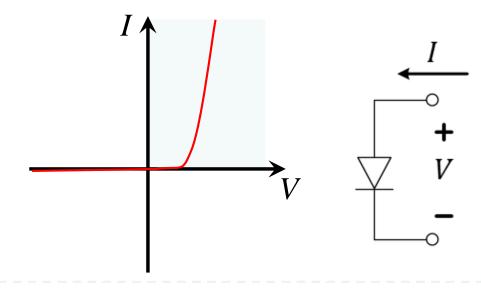


Case 2: reverse bias (cut-off)





#### L16Q1: Based on the exponential equation for IV, can the diode supply power?



#### Case 1: forward bias (V > 0)

$$e^{V/nV_{therm}} > 1$$

$$I \approx I_S(e^{V/nV_{therm}}-1)>0$$

$$P = IV > 0$$

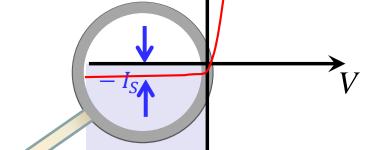
# Case 2: reverse bias (V < 0)

$$e^{V/nV_{therm}} < 1$$

$$I \approx I_S(e^{V/nV_{therm}}-1)<0$$

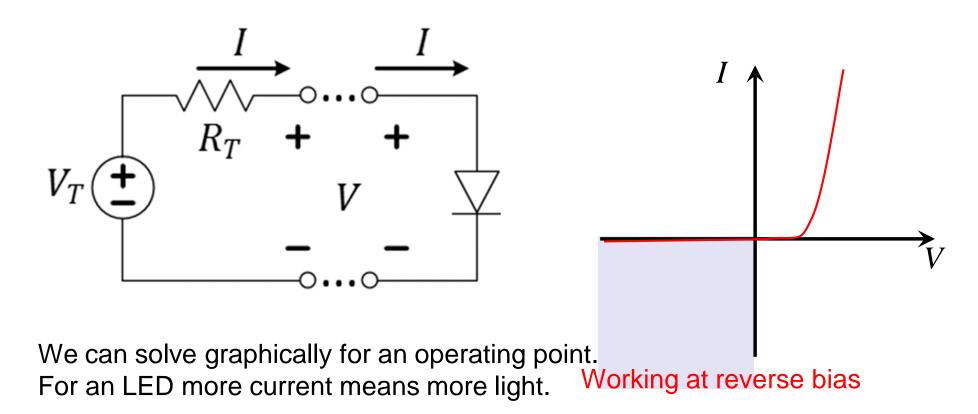
$$I \approx -I_S$$
 (for large enough  $|V|$ )

$$P = IV > 0$$





#### Connecting diode to a linear circuit

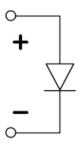


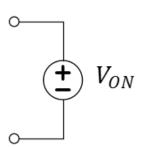
**L16Q2:** What is the current flowing through the diode if  $V_T < 0$ ?



Instead of looking for graphical solutions, we can approximate the diode with two linear segments, corresponding to diode's regimes of operation.

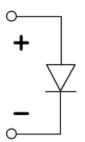
Case 1: forward bias  $(V > V_{ON})$ 

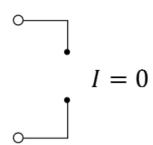


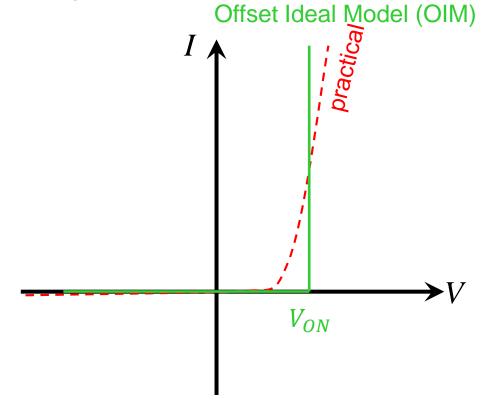


Case 2: reverse bias  $(V < V_{ON})$ 

$$I = 0$$

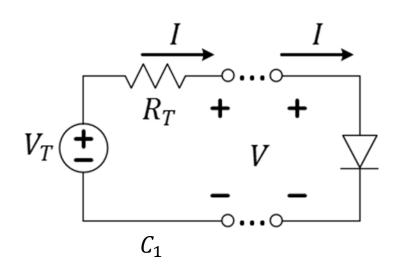


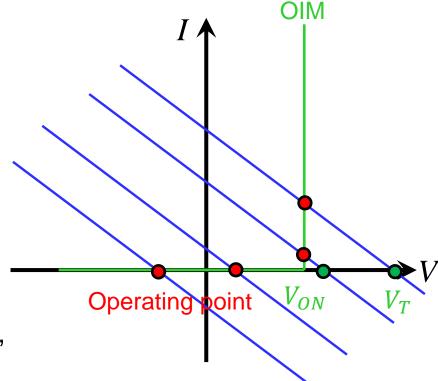






**L16Q3:** What is the minimum  $V_T$  of the connected linear circuit which causes current to flow through the diode if the piecewise linear model above is used?





For the resistor  $R_T$ , the IV characteristic is,

$$I = \frac{V_T - V}{R_T} = \frac{V_T}{R_T} - \frac{V}{R_T}$$

$$I > 0 \implies V_T > V_{on}$$



# Different diode types have different V<sub>ON</sub>

Diode Type	V <sub>ON</sub> (V)	Applications
Silicon	0.6-0.7	General; integrated circuits; switching, circuit protection, logic, rectification, etc.
Germanium	~0.3	Low-power, RF signal detectors
Schottky	0.15- 0.4	Power-sensitive, high-speed switching, RF
Red LED (GaAs)	~2	Indicators, signs, color-changing lighting
Blue LED (GaN)	~3	Lighting, flashlights, indicators
"Ideal"	0	Can neglect V <sub>ON</sub> for high voltage applications

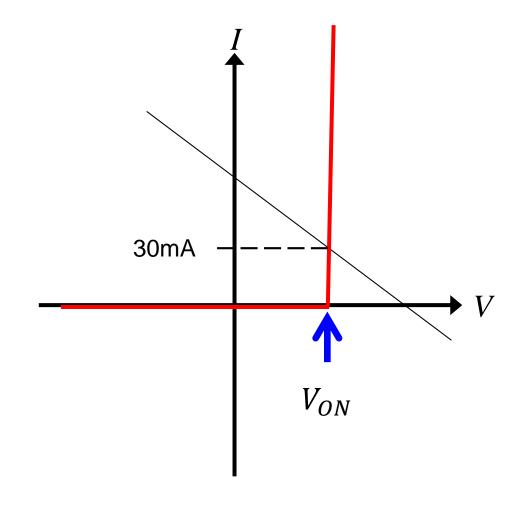


#### L16Q4: What is the power dissipated by a Ge diode if 30 mA is flowing through it?

## Germanium:

$$V_{on} \sim 0.3V$$

$$P = V_{on} \times I$$
$$= 0.3 \times 30mA$$
$$= 9mW$$



Q4:

*A.* 3 *mW* 

*B.* 9 *mW* 

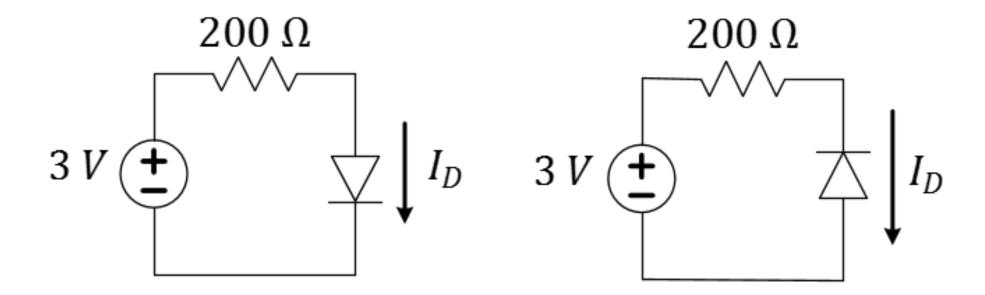
*C.* 30 *mW* 

D. 90 mW

*E.* 900 *mW* 



# Diode circuit examples (offset ideal model)



Assume offset-ideal model with  $V_{ON} = 0.7$  (common Si diodes)

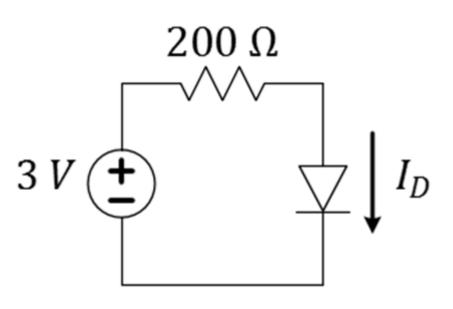
L16Q5: What is the current through the diode in the top left circuit?

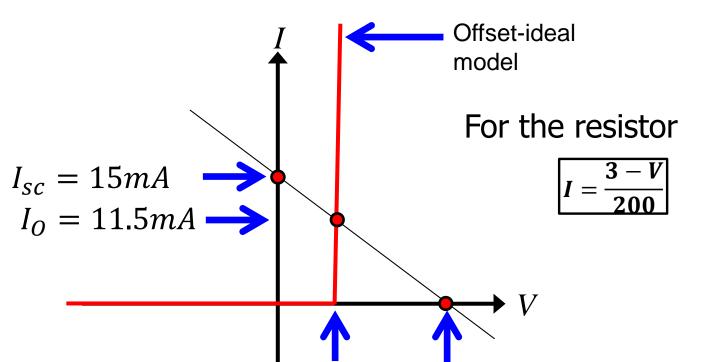
L16Q6: What is the current through the diode in the top right circuit?



#### L16Q5: What is the current through the diode?

Assume offset-ideal model with  $V_{ON} = 0.7$  (common Si diodes)





0.7V

## **FORWARD BIAS**

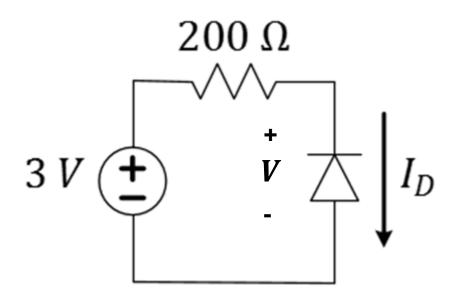
$$I_O = I_{SC} - \frac{V_{ON}}{R} = 0.015 - \frac{0.7}{200} = 11.5 mA$$

 $V_T = V_{oc} = 3V$ 



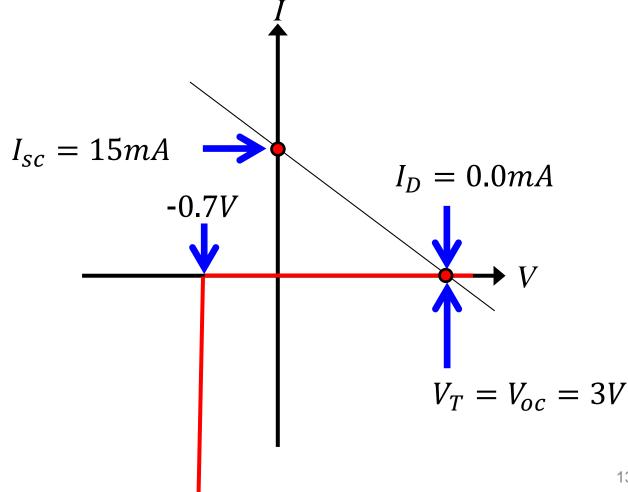
#### L16Q6: What is the current through the diode?

Assume offset-ideal model with  $V_{ON} = 0.7$  (common Si diodes)



## **REVERSE BIAS**

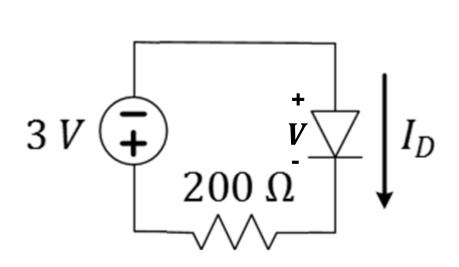
$$I_D = \frac{3-V}{200}$$





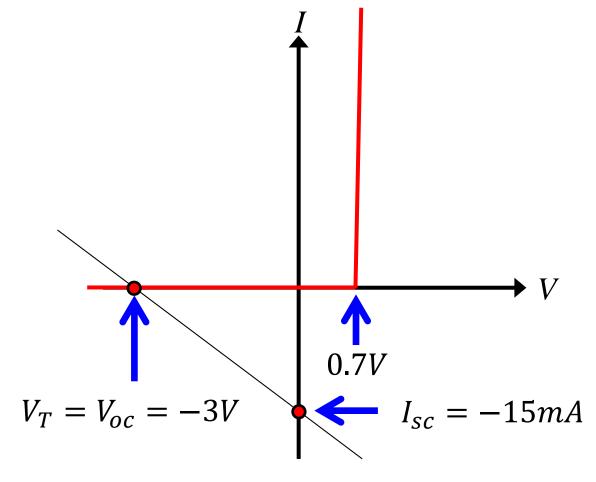
#### **L16Q6:** What is the current through the diode?

Assume offset-ideal model with  $V_{ON} = 0.7$  (common Si diodes)



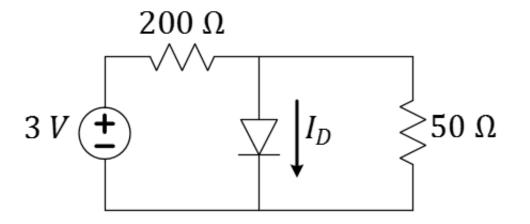
## **REVERSE BIAS**

$$I_D = \frac{-3 - V}{200}$$





# Diode circuit examples (offset ideal model)



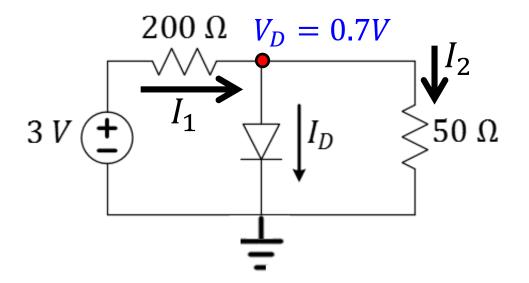
Assume offset-ideal model with  $V_{ON} = 0.7V$  (common Si diodes)

L16Q7: What is the current through the diode in the circuit?

$$I_D =$$
 $A. -11.5 mA$ 
 $B. -2.5 mA$ 
 $C. 0 mA$ 
 $D. +2.5 mA$ 
 $E. +11.5 mA$ 



#### L16Q7: What is the current through the diode in the circuit?



Assume offset-ideal model with  $V_{ON} = 0.7V$ 

Assume diode is conducting:

$$I_1 = \frac{(3-0.7)}{200} = \frac{2.3}{200} = 11.5 mA$$

$$I_2 = \frac{0.7}{50} = 14mA$$

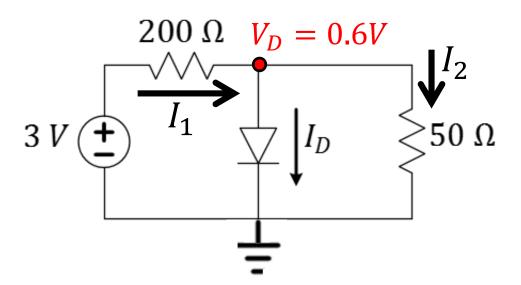
From KCL

$$I_D = I_1 - I_2 = -2.5 mA$$

NOT PHYSICAL → diode does not conduct



#### L16Q7: What is the current through the diode in the circuit?



Assume offset-ideal model with  $V_{ON} = 0.7V$ 

Assume diode is reverse biased:

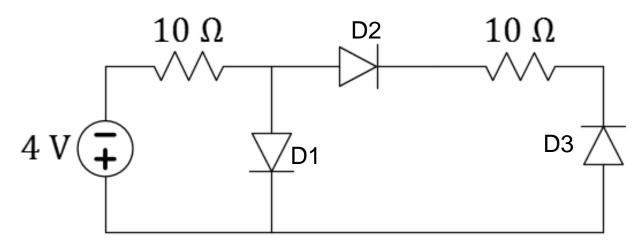
$$I_D = 0A$$
 $I_1 = I_2 = \frac{3}{250} = 12mA$ 
 $V_D = I_2 \times 50 = 0.6V$ 

$$I_D = A.$$
  $-11.5 mA$   
 $B.$   $-2.5 mA$   
 $C.$   $0 mA$   
 $D.$   $+2.5 mA$   
 $E.$   $+11.5 mA$ 

I-V operating point of the diode is (0A,0.6V)



# Back-to-back diodes in series are modeled by OIM as an open circuit

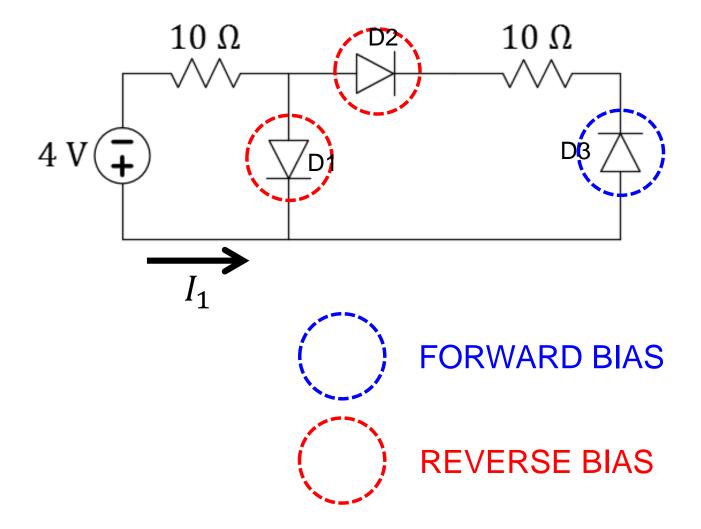


L16Q8: Assume OIM with  $V_{ON} = 0.7 \text{ V (Si)}$  What is the current through the left-most diode?

- A. 0 Amps
- *B.* 0.2 *Amps*
- *C.* 0.33 *Amps*
- *D.* 0.4 *Amps*
- *E.* 3.3 *Amps*



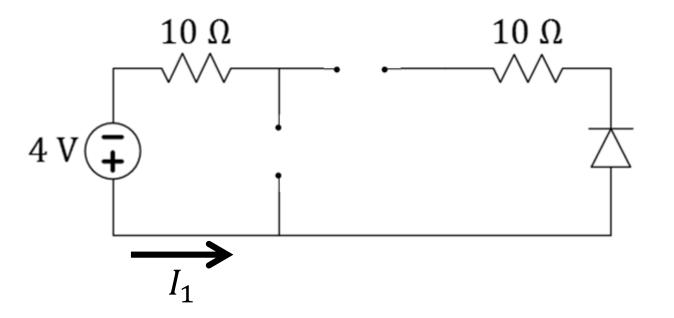
## L16Q8: Assume OIM with $V_{ON} = 0.7 \text{ V (Si)}$ What is the current through the left-most diode?



- A. 0 Amps
- *B.* 0.2 *Amps*
- *C.* 0.33 *Amps*
- *D.* 0.4 *Amps*
- *E.* 3.3 *Amps*



## L13Q8: Assume OIM with $V_{ON} = 0.7 \text{ V (Si)}$ What is the current through the left-most diode?



- A. 0 Amps
- B. 0.2 Amps
- *C.* 0.33 *Amps*
- *D.* 0.4 *Amps*
- E. 3.3 Amps



# **L16 Learning Objectives**

- a. Draw a "typical" diode IV curve and describe its shape
- Explain how to use graphical analysis to find the operating point of a diode connected to a linear circuit
- c. Describe the offset ideal diode model (open, V-source)
- d. Solve simple circuit problems with one diode, given V<sub>ON</sub>